

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **UML25S** is Designed for Class C Amplifiers in 225 to 400 MHz Military Communication Equipment.

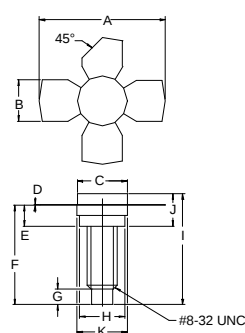
FEATURES:

- $P_G = 9.5$ dB Typical at 400 MHz
- Economical .280" Stud Package
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.0 A
V_{CBO}	60 V
V_{CEO}	30 V
V_{EBO}	3.5 V
P_{DISS}	45 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	3.0°C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10694

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 50$ mA	60			V
BV_{CBO}	$I_C = 50$ mA	60			V
BV_{EBO}	$I_E = 5$ mA	3.5			V
I_{CBO}	$V_{CB} = 30$ V			3.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	10		120	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			30	pF
P_G η_D	$V_{CC} = 28$ V $P_{OUT} = 25$ W $f = 400$ MHz	9.0	60		dB %